

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# SSM6K804R

#### 1. Applications

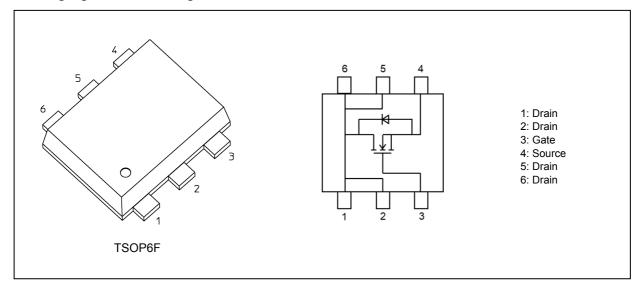
- · Power Management Switches
- · DC-DC Converters

#### 2. Features

- (1) AEC-Q101 qualified (Note 1)
- (2) 175 °C MOSFET
- (3) 4.5-V drive
- (4) Low drain-source on-resistance
  - :  $R_{DS(ON)}$  = 12 m $\Omega$  (typ.) (@ $V_{GS}$  = 4.5 V)  $R_{DS(ON)}$  = 9 m $\Omega$  (typ.) (@ $V_{GS}$  = 10 V)

Note 1: For detail information, please contact our sales.

### 3. Packaging and Pin Assignment





## 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristic	:s		Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	40	V
Gate-source voltage			$V_{GSS}$	-20/+20	
Drain current (DC)		(Note 1)	$I_D$	12	Α
Drain current (pulsed)	(t ≤ 10 μs)	(Note 1), (Note 2)	$I_{DP}$	50	
Power dissipation		(Note 3)	$P_{D}$	1.5	W
Power dissipation	(t ≤ 10 s)	(Note 3)	$P_{D}$	3	W
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	58.5	mJ
Single-pulse avalanche current			I <sub>AS</sub>	7.5	Α
Channel temperature		(Note 5)	T <sub>ch</sub>	175	℃
Storage temperature		(Note 5)	T <sub>stg</sub>	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 175 °C.
- Note 2: Pulse width  $\leq$  10  $\mu$ s, duty  $\leq$  1 %
- Note 3: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)
- Note 4:  $V_{DD}$  = 32 V,  $T_{ch}$  = 25 °C (Initial state), L = 1 mH,  $R_G$  = 25  $\Omega$
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	_	_	±100	nA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	_	_	1	μΑ
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	40	_		٧
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	37	_	_	
Gate threshold voltage	(Note 2)	$V_{th}$	$V_{DS} = 10 \text{ V}, I_{D} = 0.1 \text{ mA}$	1.4	_	2.4	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 4 A, V <sub>GS</sub> = 4.5 V	_	12	18	mΩ
			I <sub>D</sub> = 4 A, V <sub>GS</sub> = 10 V	_	9	12	

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 2: Let V<sub>th</sub> be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20 V , V <sub>GS</sub> = 0 V,	_	1110	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	26	_	
Output capacitance	Coss		_	245		
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD} = 20 \text{ V}, I_{D} = 1 \text{ A},$ $V_{GS} = 0 \text{ to } 4.5 \text{ V}, R_{GS} = 30 \Omega$	_	24	_	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty ≤ 1 %, Input t <sub>r</sub> , t <sub>f</sub> < 5 ns, Ground source, see Chapter 5.3	_	35	_	

#### 5.3. Switching Time Test Circuit

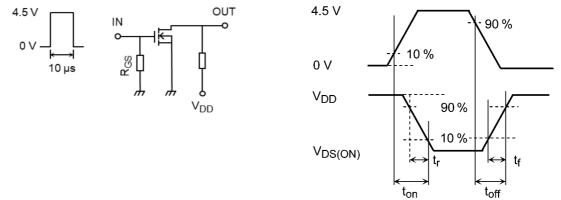


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}$ = 20 V, $I_{D}$ = 12 A,	_	7.5	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$V_{GS} = 4.5 \text{ V}$	_	2.9	_	
Gate-drain charge	Q <sub>gd</sub>		_	2.8	_	

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## 5.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (Note 1	) V <sub>DSF</sub>	I <sub>D</sub> = -12 A, V <sub>GS</sub> = 0 V	_	-0.85	_	V

Note 1: Pulse measurement.

## 6. Marking

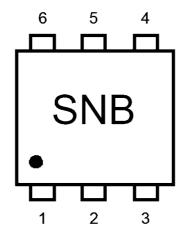


Fig. 6.1 Marking



#### 7. Characteristics Curves (Note)

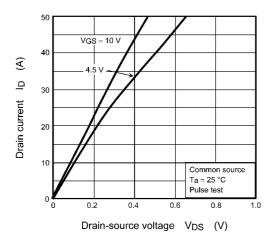


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>

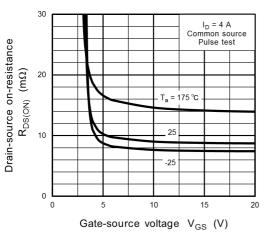


Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

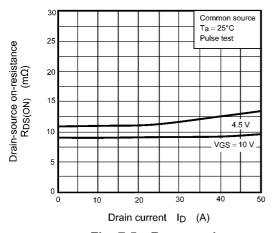


Fig. 7.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

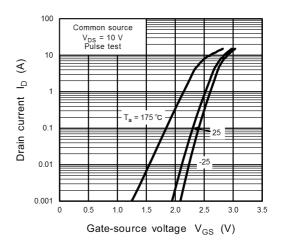


Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

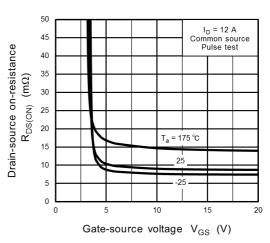


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

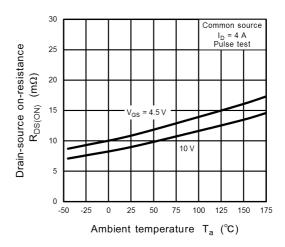


Fig. 7.6 R<sub>DS(ON)</sub> - T<sub>a</sub>



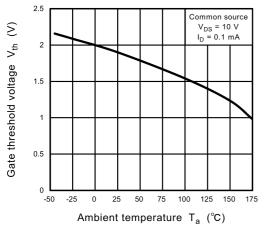
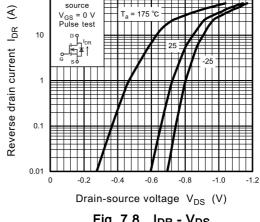


Fig. 7.7 V<sub>th</sub> - T<sub>a</sub>



100

Fig. 7.8 IDR - VDS

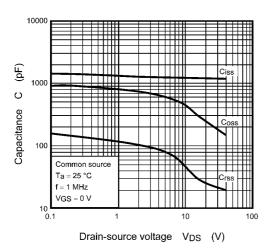


Fig. 7.9 C - V<sub>DS</sub>

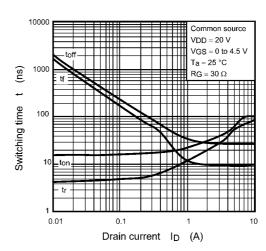


Fig. 7.10 t - I<sub>D</sub>

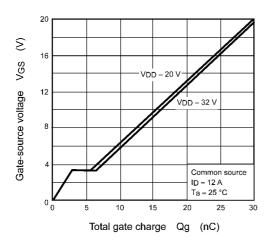


Fig. 7.11 Dynamic Input Characteristics

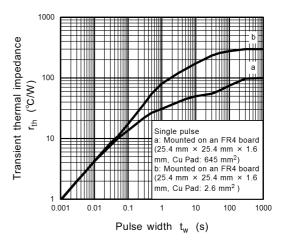
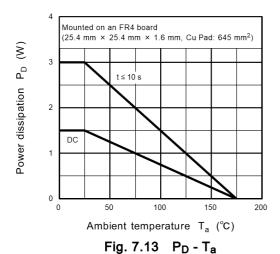


Fig. 7.12 rth - tw





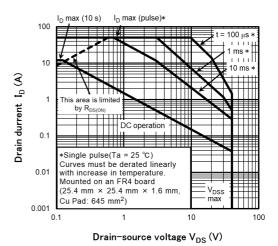


Fig. 7.14 Safe Operating Area

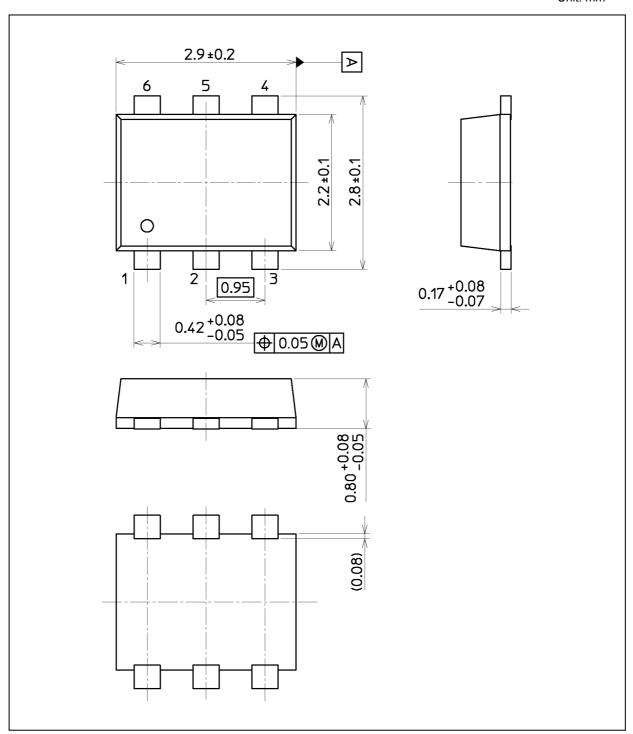
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Rev.2.0



## **Package Dimensions**

Unit: mm



Weight: 0.016 g (typ.)

Package Name(s)
TOSHIBA: 2-3AC1A
Nickname: TSOP6F



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